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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	NEW 10/758,009
				Filing Date	January 7, 2004 01/16/04
				First Named Inventor	Jiutao Li
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned Featy
Sheet	1	of	9	Attorney Docket Number	M4065.0609/P609/P609-D

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
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		Country Code ³	Number ⁴ -Kind Code ⁵ (if known)			
	BA	WO	02/21542*	03/14/2002	Kozicki et al.	
	BB	WO	00/48196*	08/17/2000	Kozicki et al.	
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
Examiner Signature	<i>Paul L. Fenty</i>	Date Considered	3/17/5
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
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	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge _{25-x} Sb _x , Appl. Phys. A 55 (1992) 167-169.	
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	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
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Sheet	4	of	9	Attorney Docket Number	M4065.0609/P609/P609-D

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		Application Number	NEW 101758,009		
		Filing Date	January 7, 2004 01/16/04		
		First Named Inventor	Jiutao Li		
		Group Art Unit	N/A 2815		
		Examiner Name	Not Yet Assigned i-r-ty		
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		Group Art Unit	N/A 2815
		Examiner Name	Not Yet Assigned Fein
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Examiner Signature	<i>Not Yet Assigned Fein</i>	Date Considered	3/17/05
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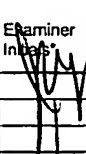
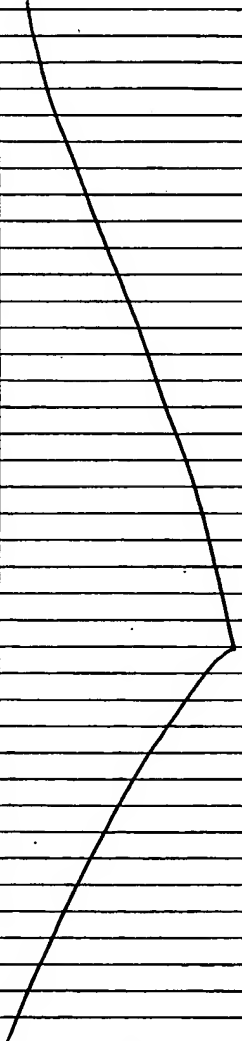

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			First Named Inventor	Li Jiutao	
			Art Unit	2814 2815	
			Examiner Name	Not Yet Assigned Feuty	
Sheet	1	of	4	Attorney Docket Number	M4065.0609/P609-D

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Examiner Initials	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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			Application Number	10/758,009	
			Filing Date	January 16, 2004	
			First Named Inventor	Li Jiutao	
			Art Unit	2811 3815	
			Examiner Name	Not Yet Assigned <i>Ferty</i>	
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Examiner Signature	<i>[Signature]</i>	Date Considered	3/17/5
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